

AMENDMENT TO THE CLAIMS

Claims 1-65 (canceled)

66. (previously presented) An electrically programmable memory element, comprising:

a first dielectric layer having an opening, said opening having a sidewall surface and a bottom surface;

a conductive layer disposed on the sidewall surface of said opening, said conductive layer having a raised portion on said sidewall surface extending from an upper edge of said conductive layer to a peak, said conductive layer having a lateral thickness of less than 500 Angstroms at said upper edge, said raised portion having a lateral thickness of less than 500 Angstroms at said peak and a lateral width of less than 500 Angstroms at said peak; and

a programmable resistance memory material electrically coupled to said raised portion.

67. (previously presented) The memory element of claim 66, further comprising a second dielectric layer disposed within said opening on said conductive layer.

68. (previously presented) The memory element of claim 66, wherein said memory material is a phase-change material comprising a chalcogen element.

Claim 69-83 (canceled)